

Homework 4 (Due date: 10/25)

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HW4.1: (20 points)

Using a long-channel model, **prove** that, in strong inversion, the transistor  $M_R$  behaves like a resistor ( $R_{on,R}$ ) with its resistance,

$$R_{on,R} = \frac{(W/L)_C}{(W/L)_R} \frac{1}{g_{m,C}}$$

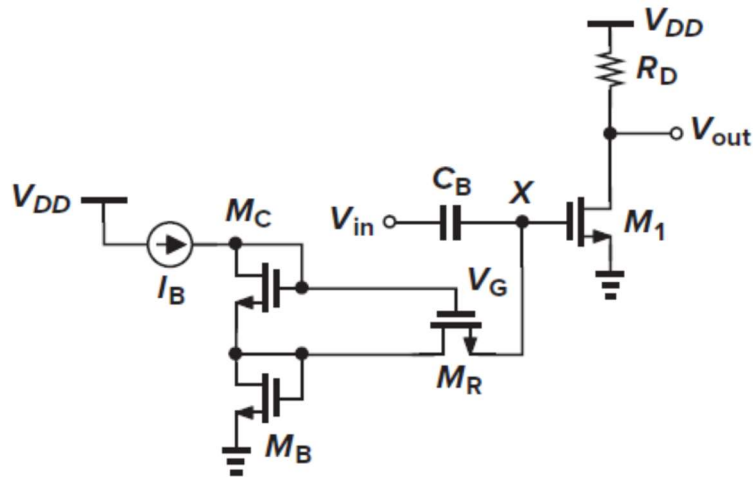


Fig. 4.1

HW4.2: (30 points)

The circuit of Fig. 4.2 is designed with  $(W/L)_{1,2} = 8/2$ ,  $(W/L)_{3,0} = 8/2$ , and  $I_{REF} = 100 \mu A$ .

Assume  $\mu_n C_{ox} = 800 \mu A/V^2$ ,  $V_{DD} = 3V$  and  $\gamma = 0$ .  **$V_{TH} = 0.7V$**

- Determine  $V_X$  and the acceptable range of  $V_b$ .
- Estimate the deviation of  $I_{out}$  from  **$100 \mu A$**  if the drain voltage of  $M_3$  is higher than  $V_X$  by 1 V, if  $\lambda = 0.1 V^{-1}$ .
- How to design  $V_b$  to have a minimum drain voltage of  $M_3$ ?

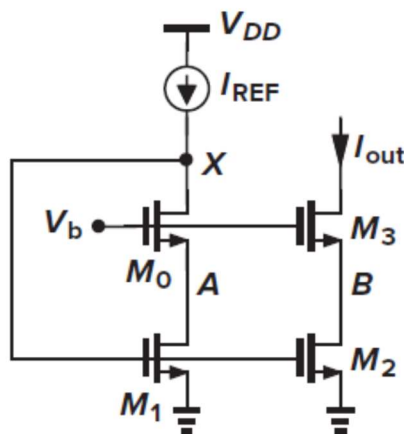


Fig. 4.2

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### HW4.3 (30 points)

In the circuit shown in Fig. 4.3, a source follower using a wide transistor and a small bias current is inserted in series with the gate of  $M_3$  so as to bias  $M_2$  at the edge of saturation. Assuming  $M_0$ – $M_3$  are identical and  $\lambda \neq 0$ , estimate the mismatch between  $I_{out}$  and  $I_{REF}$  if (a)  $\gamma = 0$ , (b)  $\gamma \neq 0$ .

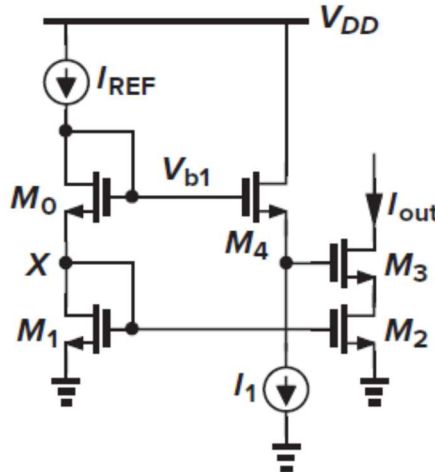


Fig. 4.3

### HW4.4: (20 points)

The circuit shown in Fig. 4.4 exhibits a **negative input inductance**. Calculate the input impedance of the circuit and identify the inductive component.

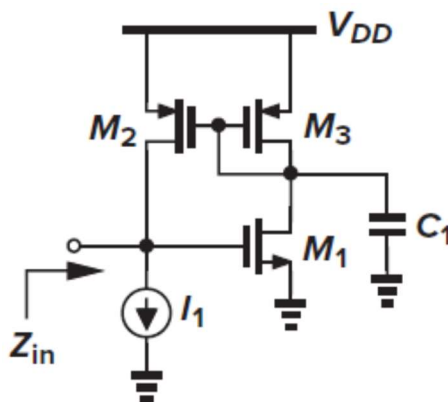


Fig. 4.4